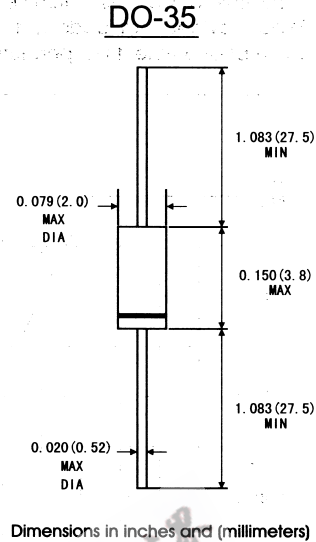


FEATURES

- The zener voltage are graded according to the international E24 standard .Other voltage tolerance and higher zener voltage on request.

MECHANICAL DATA

- Case:** DO-35 glass case
- Polarity:** Color band denotes cathode end
- Weight:** Approx. 0.13gram



ABSOLUTE MAXIMUM RATINGS(LIMITING VALUES)(TA=25°C)

	Symbols	Value	Units
Zener current see table "Characteristics"			
Power dissipation at TA=50°C	P _{tot}	500 ¹⁾	mW
Junction temperature	T _J	175	°C
Storage temperature range	T _{STG}	-65 to + 175	°C

1)Valid provided that at a distance of 8mm from case are kept at ambient temperature

ELECTRICAL CHARACTERISTICS(TA=25°C)

	Symbols	Min.	Typ.	Max.	Units
Thermal resistance junction to ambient	R _{θJA}			300 ¹⁾	K/W
Forward voltage at I _F =100mA	V _F			1	V

1)Valid provided that leads at a distance of 8mm from case are kept at ambient temperature



BXZ55... SILICON PLANAR ZENER DIODES

Type	Zener Voltage Range ¹⁾			Dynamic resistance			Reverse leakage current			Temp coefficient of zener voltage
	V _{ZNOM}	I _{ZT} for V _{ZT} 2)		r _{zjt} and r _{zjk} at I _{zk}			I _R and I _{R2} at V _R			TK _{VZ}
	V	mA	V	Ω	Ω	mA	μA	μA	V	%/K
BZX 55/C 0V8 3)	0.8		0.73.0.83	<8	<50		-	-	-	-0.26...-0.23
BZX 55/C 2V0	2.0		1.9.2.1	<85	<600	1	<100	<200	<1	-0.09...-0.06
BZX 55/C 2V4	2.4		2.28.2.56				<50	<100		
BZX 55/C 2V7	2.7		2.5.2.9				<10	<50		
BZX 55/C 3V0	3		2.8.3.2				<4	<40		
BZX 55/C 3V3	3.3		3.1.3.5				<2	<40		-0.08...-0.05
BZX 55/C 3V6	3.6		3.4.3.8				<1	<20		
BZX 55/C 3V9	3.9		3.7.4.1				<0.5	<10		-0.06...-0.03
BZX 55/C 4V3	4.3		4.0.4.6				<60			-0.05...+0.02
BZX 55/C 4V7	4.7		4.4.5.0				<35	<550		-0.02...+0.02
BZX 55/C 5V1	5.1		4.8.5.4				<25	<450		-0.05...+0.05
BZX 55/C 5V6	5.6	5	5.2.6.0	<10	<200	2.0	0.03.0.06			
BZX 55/C 6V2	6.2		5.8.6.6	<8	<150	3.0	0.03.0.07			
BZX 55/C 6V8	6.8		6.4.7.2	<7	<50	5.0	0.03.0.07			
BZX 55/C 7V5	7.5		7.0.7.9	<7		6.2	0.03.0.08			
BZX 55/C 8V2	8.2		7.7.8.7	<10		6.8	0.03.0.09			
BZX 55/C 9V1	9.1		8.5.9.6	<15	<70	<0.1	<2	7.5	0.03.0.1	
BZX 55/C 10	10		9.4.10.6	<20	<70			8.2	0.03.0.11	
BZX 55/C 11	11		10.4.11.6	<20	<90			9.1		
BZX 55/C 12	12		11.4.12.7	<26	<110			10.0		
BZX 55/C 13	13		12.4.14.1	<30	<110			11.0		
BZX 55/C 15	15		13.8.15.6	<40	<170			12		
BZX 55/C 16	16		15.3.17.1	<50	<170			13		
BZX 55/C 18	18		16.8.19.1	<55	<220			15		
BZX 55/C 20	20		18.8.21.2							



BZX55... SILICON PLANAR ZENER DIODES

BZX 55/C 22	22	5	20.8.23.3	<55	<220	1	<2	16	0.04.0.12			
BZX 55/C 24	24		22.8.25.6	<80				18				
BZX 55/C 27	27		25.1.28.9	<80				20				
BZX 55/C 30	30		28.32					22				
BZX 55/C 33	33		31.35					24				
BZX 55/C 36	36		34.38					27				
BZX 55/C 39	39	2.5	37.41	<500	0.5	<0.1	<5	30				
BZX 55/C 43	43		40.46	<500			33					
BZX 55/C 47	47		44.50	<600			36					
BZX 55/C 51	51		48.54	<700			39					
BZX 55/C 56	56		52.60	<700			43					
BZX 55/C 62	62		58.66	<1000			47					
BZX 55/C 68	68		64.72				51					
BZX 55/C 75	75		70.79				56					
BZX 55/C 82	82		77.87				<1500	62				
BZX 55/C 91	91		1	85.96			<2000	0.1		<10	68	0.05.0.12
BZX 55/C 100	100			94.106			<5000				75	
BZX 55/C 110	110			104.116			<5000				82	
BZX 55/C 120	120			114.127			<5500				91	
BZX 55/C 130	130			124.141			<6000				100	
BZX 55/C 150	150	138.156		<6500	110							
BZX 55/C 160	160	153.171		<7000	120							
BZX 55/C 180	180	168.191		<8500	130							
BZX 55/C 200	200	188.212		<10000	150							

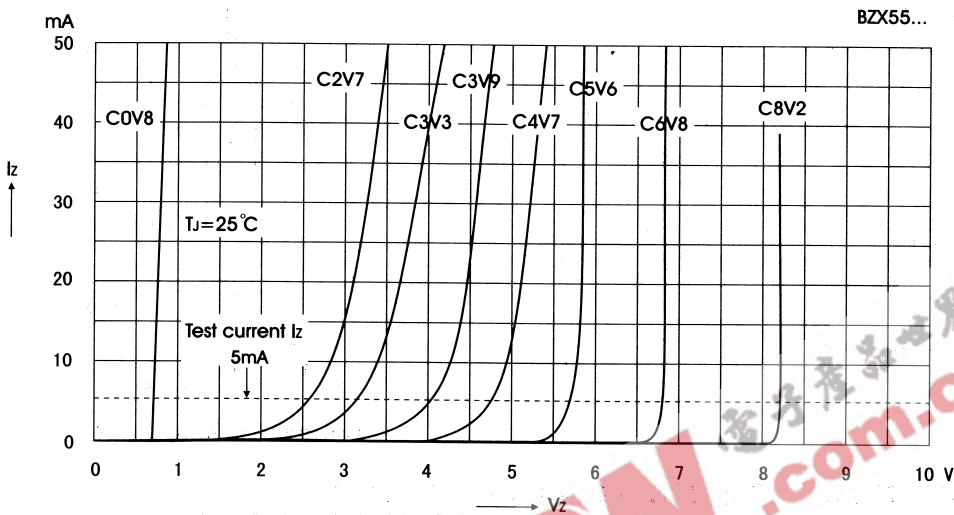
1) Tested with pulses $t_p=20ms$

2) Valid provided that leads are kept at ambient temperature at a distance of 8mm from case

3) The BZX55-C0V8 is silicon diode with operation in forward direction. Hence, the index of all parameters should be 'F' instead of 'Z'. Connect the cathode lead to the negative pole.

BXZ55... SILICON PLANAR ZENER DIODES

BREAKDOWN CHARACTERISTICS AT T_J=CONSTANT(PULSED)



BREAKDOWN CHARACTERISTICS AT T_J=CONSTANT(PULSED)

